



SK08N65B-T/TF

N-Channel MOSFET

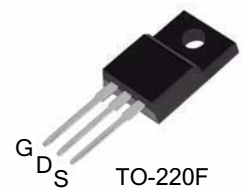
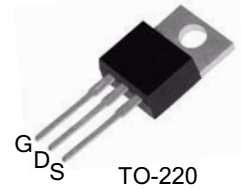
V_{DSS}	$R_{DS(ON)}$ (Typ.)	I_D
650 V	0.91Ω	8 A

Applications:

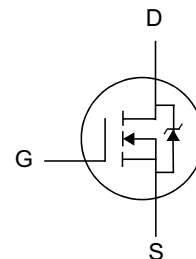
- Adaptor
- Charger
- SMPS Power Supply
- LCD Panel Power

Features:

- RoHS Compliant
- Low ON Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve



Packages



Ordering Information

PART NUMBE	SK08N65B-T	SK08N65B-TF
PACKAGE	TO-220	TO-220F

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	SK08N65B-T	SK08N65B-TF	Units
V _{DSS}	Drain-to-Source Voltage (NOTE *1)	650		V
I _D	Continuous Drain Current	8.0	8.0*	A
I _D @ 100°C	Continuous Drain Current	Figure 3		
I _{DM}	Pulsed Drain Current, V _{GS} @ 10V (NOTE *2)	Figure 6		
P _D	Power Dissipation	120	42	W
	Derating Factor above 25 °C	0.96	0.34	W/°C
V _{GS}	Gate-to-Source Voltage	± 30		V
E _{AS}	Single Pulse Avalanche Energy L=10 mH	450		mJ
I _{AS}	Pulsed Avalanche Rating	Figure 8		A
dv/dt	Peak Diode Recovery dv/dt (NOTE *3)	5.0		V/ns
T _L T _{PKG}	Maximum Temperature for Soldering Leads at 0.063 in (1.6 mm) from Case for 10 seconds Package Body for 10 seconds	300 260		°C
T _J and T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150		

* Drain Current Limited by Maximum Junction Temperature

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	SK08N65B-T	SK08N65B-TF	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	1.04	2.98	$^\circ\text{C/W}$	Drain lead soldered to water cooled heatsink, P_D adjusted for a peak junction temperature of $+150^\circ\text{C}$.
$R_{\theta JA}$	Junction-to-Ambient	62	100		1 cubic foot chamber, free air.



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OFF Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	650	--	--	V	$V_{GS}=0V$, $I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient, Figure 11.	--	0.50	--	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1.0	μA	$V_{DS}=650V$, $V_{GS}=0V$
		--	--	250		$V_{DS}=520V$, $V_{GS}=0V$ $T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	--	--	100	nA	$V_{GS}=+30V$
	Gate-to-Source Reverse Leakage	--	--	-100		$V_{GS}=-30V$

ON Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance Figure 9 and 10.	--	0.91	1.3	Ω	$V_{GS}=10V$, $I_D=4.0A$ (NOTE *4)
$V_{GS(TH)}$	Gate Threshold Voltage, Figure 12.	2.0	--	4.0	V	$V_{DS}=V_{GS}$, $I_D=250\mu A$
gfs	Forward Transconductance	--	10	--	S	$V_{DS}=20V$, $I_D=8A$ (NOTE *4)

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
C_{iss}	Input Capacitance	--	1240	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0\text{MHz}$ Figure 14
C_{oss}	Output Capacitance	--	110	--		
C_{rss}	Reverse Transfer Capacitance	--	14	--		
Q_g	Total Gate Charge	--	28	--	nC	$V_{DD}=325V$ $I_D=8A$, $V_{GS}=10V$ Figure 15
Q_{gs}	Gate-to-Source Charge	--	5.6	--		
Q_{gd}	Gate-to-Drain ("Miller") Charge	--	11.2	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	13	--	ns	$V_{DD}=325V$ $I_D=8A$ $V_{GS}=10V$ $R_G=9.1\Omega$
t_{rise}	Rise Time	--	15	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	40	--		
t_{fall}	Fall Time	--	22	--		



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Source-Drain Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	--	--	8	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	32	A	
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_S=8\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	--	555	--	ns	$V_{GS}=0\text{V}$, $V_{DD}=60\text{V}$ $I_F=8\text{A}$, $di/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse Recovery Charge	--	3.4	--	μC	

Notes:

- *1. $T_J = +25^\circ\text{C}$ to $+150^\circ\text{C}$.
- *2. Repetitive rating; pulse width limited by maximum junction temperature.
- *3. $I_{SD} = 8\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$.
- *4. Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.



Typical Characteristics

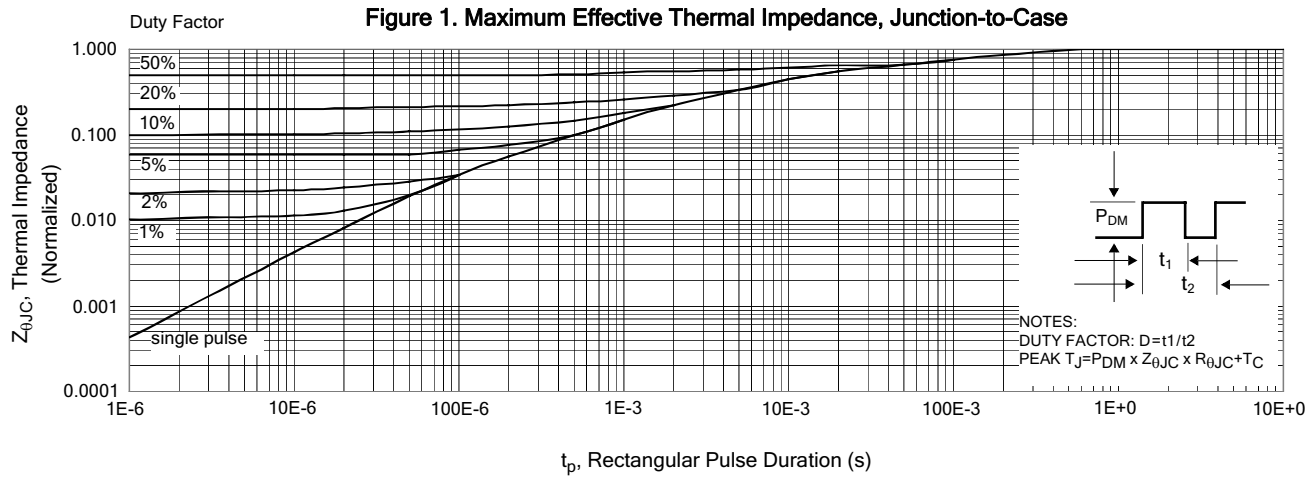


Figure 2. Maximum Power Dissipation vs Case Temperature

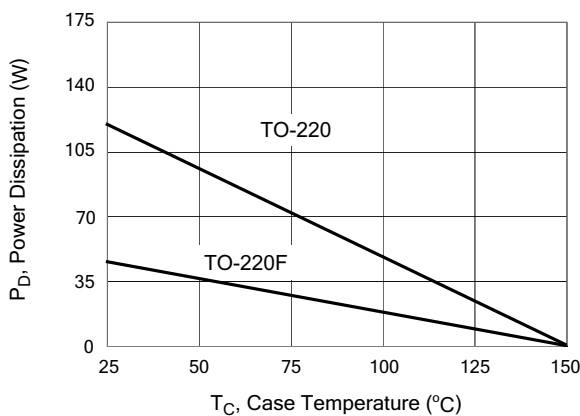


Figure 3. Maximum Continuous Drain Current vs Case Temperature

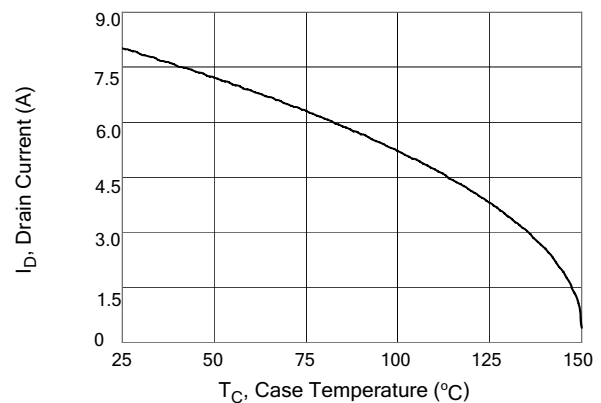


Figure 4. Typical Output Characteristics

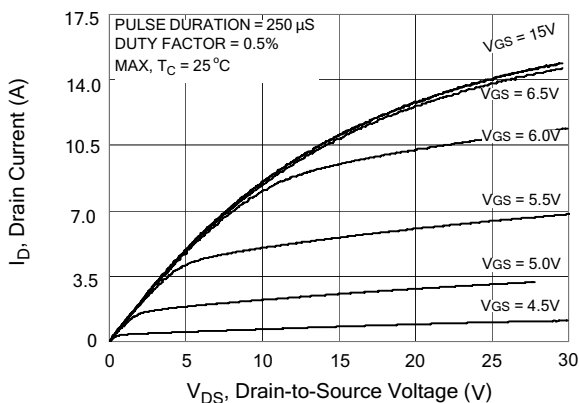
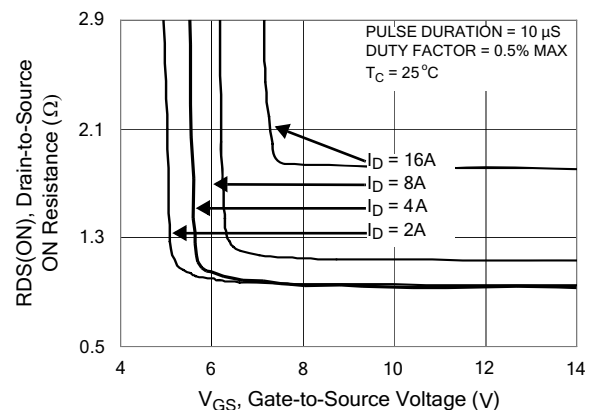
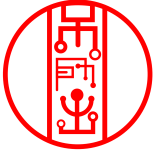


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current





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Figure 6. Maximum Peak Current Capability

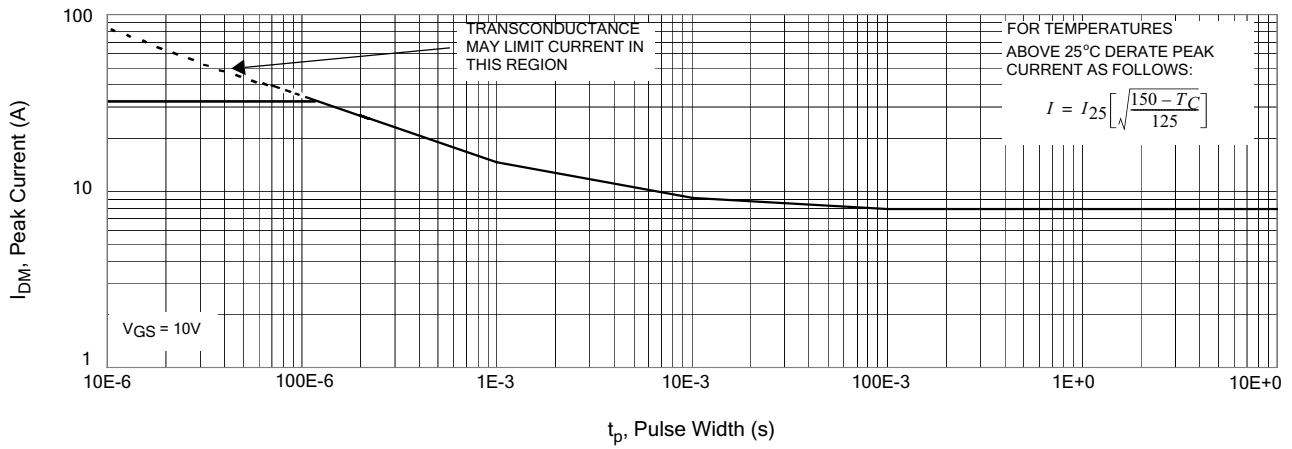


Figure 7. Typical Transfer Characteristics

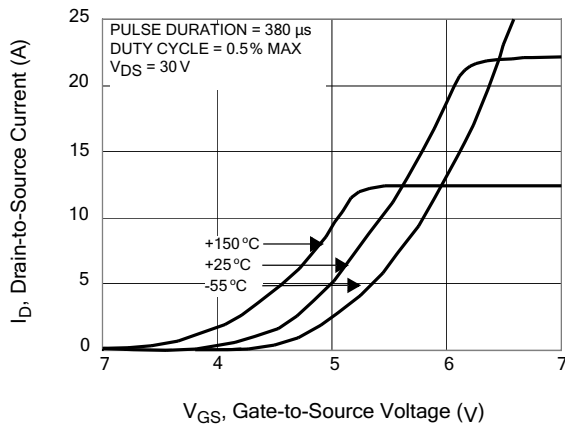


Figure 8. Unclamped Inductive Switching Capability

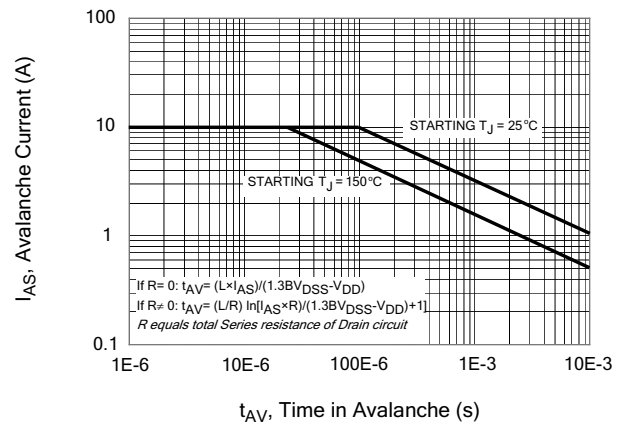


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

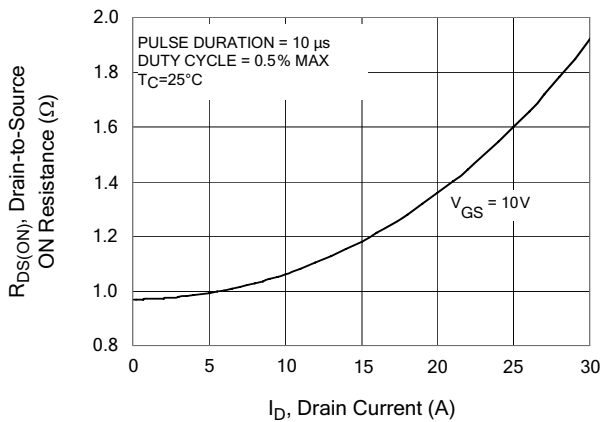
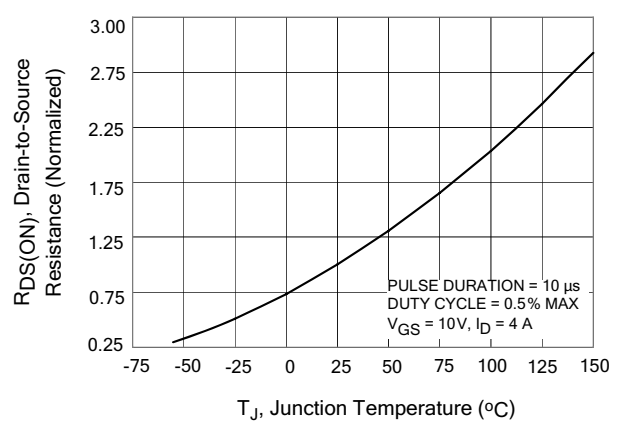
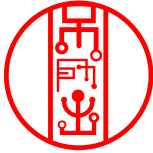


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature





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Figure 11. Typical Breakdown Voltage vs Junction Temperature

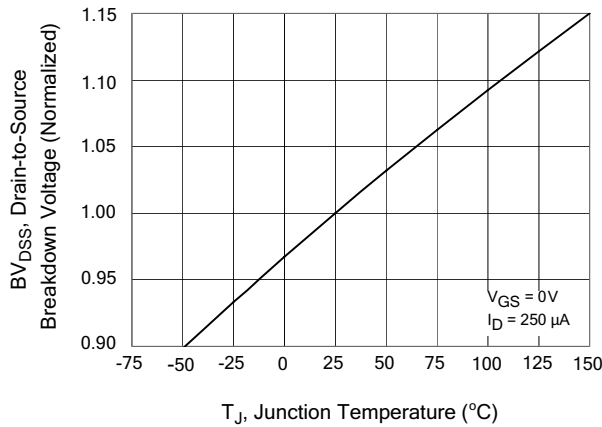


Figure 12. Typical Threshold Voltage vs Junction Temperature

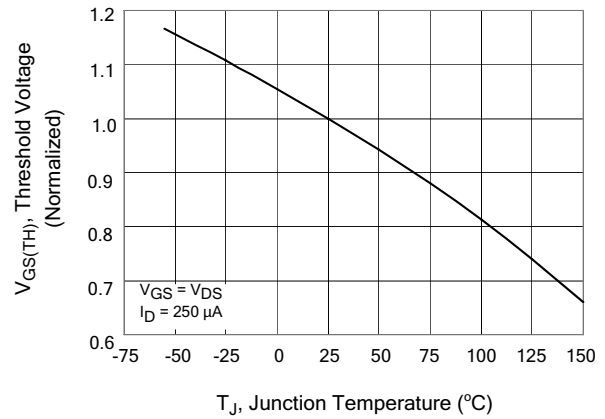


Figure 13. Maximum Forward Bias Safe Operating Area

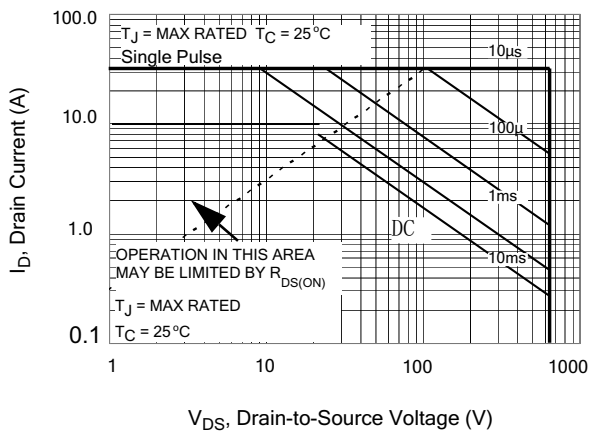


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

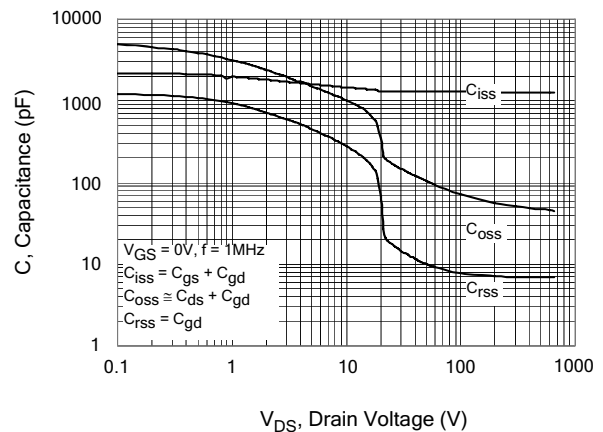


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

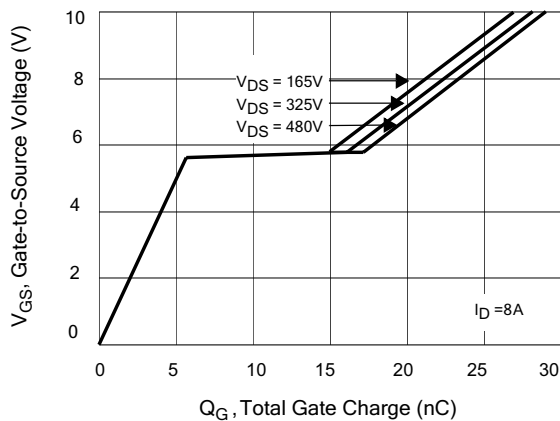
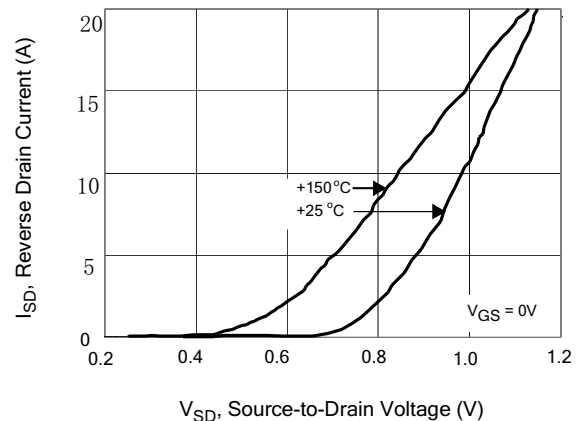


Figure 16. Typical Body Diode Transfer Characteristics





TEST CIRCUITS AND WAVEFORMS

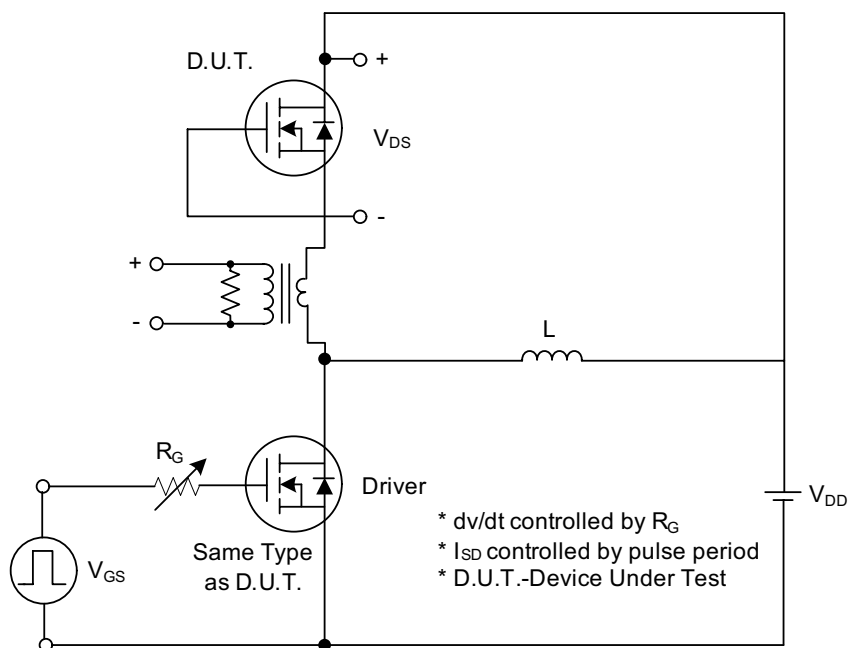


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

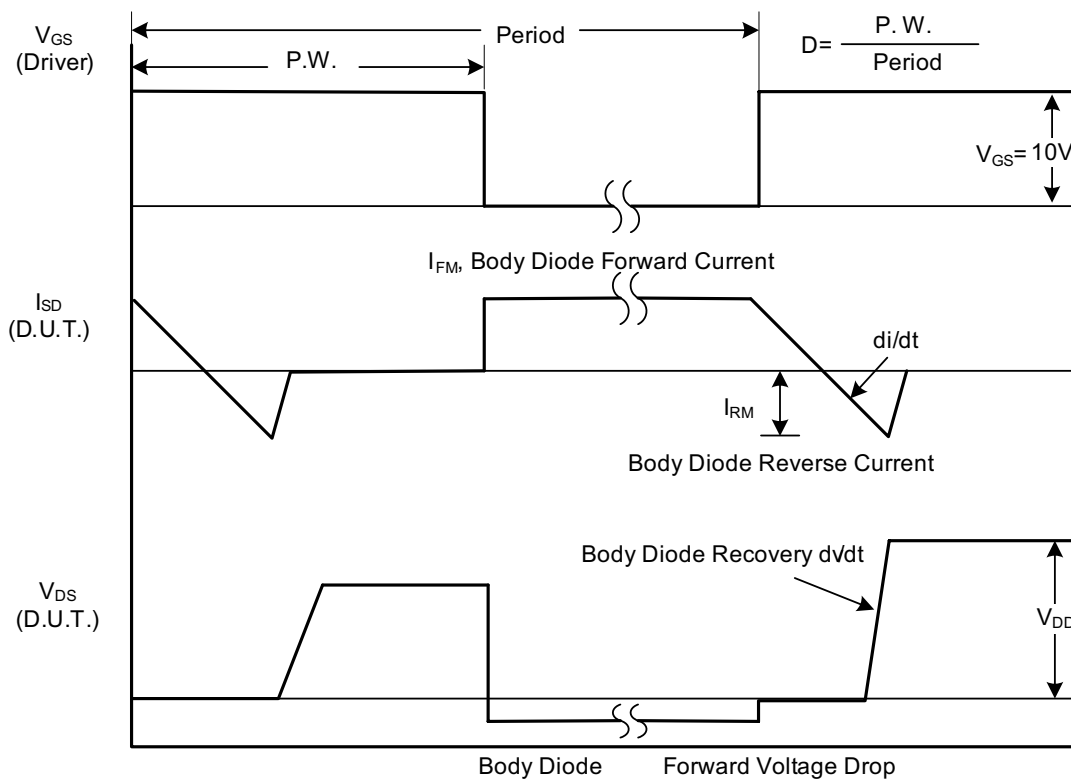


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms



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TEST CIRCUITS AND WAVEFORMS (Cont.)

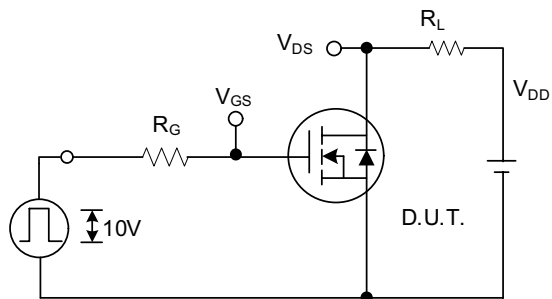


Fig. 2.1 Switching Test Circuit

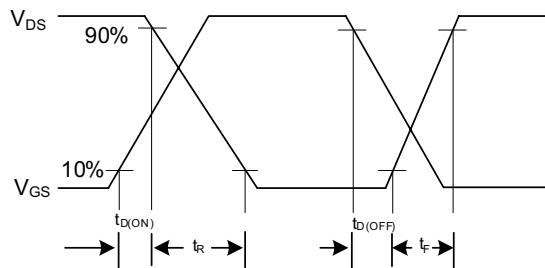


Fig. 2.2 Switching Waveforms

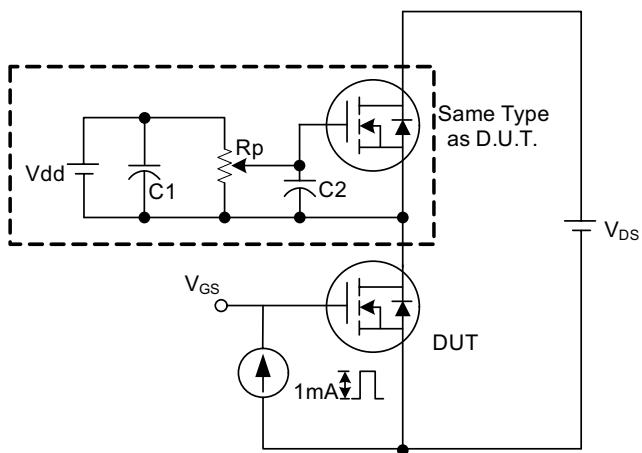


Fig. 3.1 Gate Charge Test Circuit

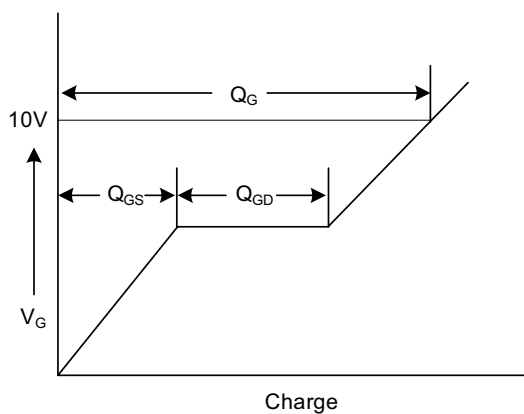


Fig. 3.2 Gate Charge Waveform

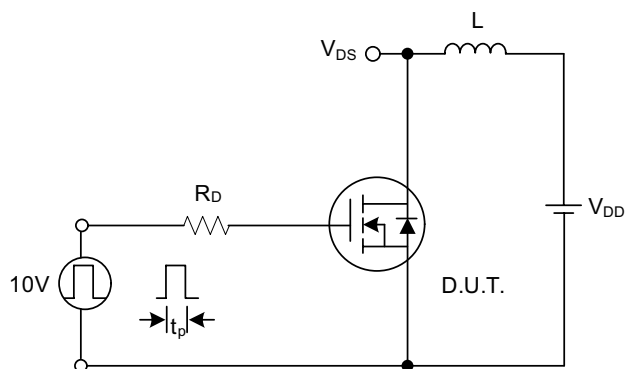


Fig. 4.1 Unclamped Inductive Switching Test Circuit

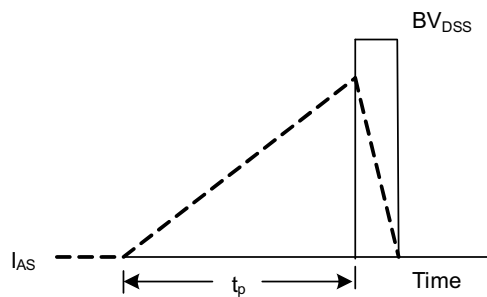


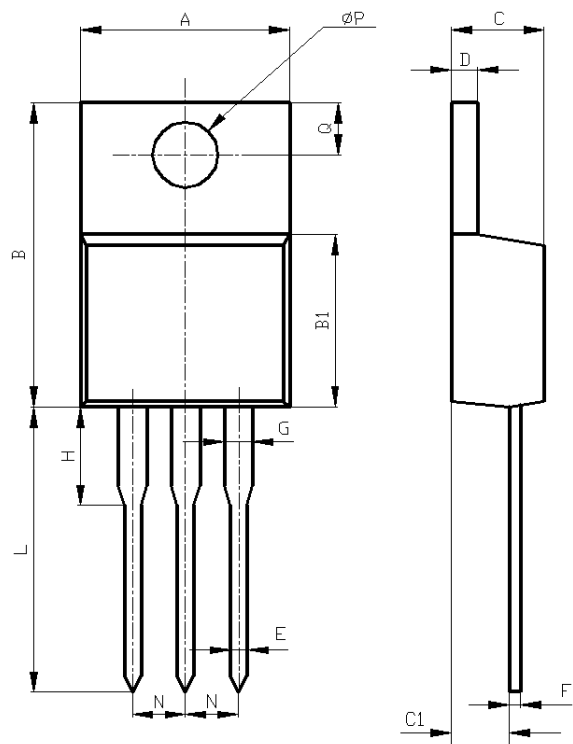
Fig. 4.2 Unclamped Inductive Switching Waveforms



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PACKAGE OUTLINE

TO-220



: mm

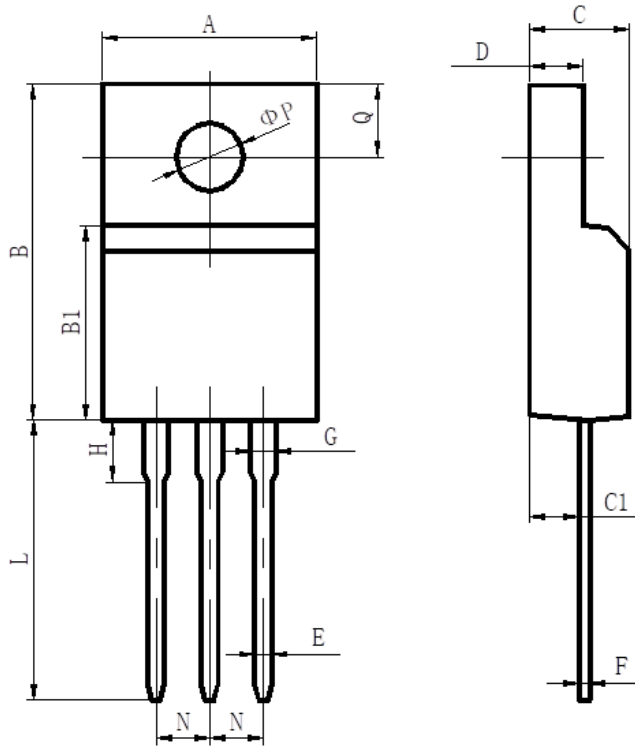
	Unit (mm)	
	MIN	MAX
A	10.1	10.5
B	15.2	15.6
B1	9.00	9.40
C	4.40	4.60
C1	2.40	3.00
D	1.20	1.40
E	0.70	0.90
F	0.40	0.60
G	1.17	1.37
H	3.30	3.80
L	13.1	13.7
N	2.34	2.74
Q	2.40	3.00
Φ P	3.70	3.90



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PACKAGE OUTLINE

TO-220F



	Unit (mm)	
	MIN	MAX
A	9.70	10.30
B	15.50	16.10
B1	8.99	9.39
C	4.40	4.80
C1	2.15	2.55
D	2.50	2.90
E	0.70	0.90
F	0.40	0.60
G	1.12	1.42
H	3.40	3.80
L	12.6	13.6
N	2.34	2.74
Q	3.15	3.55
ΦP	3.00	3.30